

CLAIM AMENDMENTS

1. (Currently Amended) A high power semiconductor device comprising:  
~~a plurality of gate electrodes;~~  
an active region having an approximately rectangular shape, located on a semiconductor substrate; and  
at least one cell including:  
a drain electrode ~~located on~~ extending across at least part of the active region;  
~~and~~  
first and second source electrodes extending across at least part of the active region and disposed on the opposite sides of the drain electrode ~~so that, with~~ the first and the second source electrodes ~~face~~ facing each other ~~across at least some of the;~~  
first and second gate electrodes, wherein extending across at least part of the active region and respectively interposed between the drain electrode and the first and second gate electrodes; and  
first and second source via holes located outside of and on opposite sides of the active region and respectively electrically connected to the first and second source electrodes so that currents carried by the first and the second source electrodes flow in opposite directions from each other.

Claim 2 (Cancelled).

3. (Currently Amended) The semiconductor device according to claim ~~21~~, including ~~source wires connected to the first and second source via holes~~ a plurality of the cells, wherein all of the source wires ~~being~~ are connected to the source via holes by air bridges which extend generally along a width direction of the source electrodes ~~connected to the source wires.~~

4. (Currently Amended) The semiconductor device according to claim ~~21~~, wherein the first source via hole is offset from a position which faces the second source via hole across the active region.

5. (Currently Amended) The semiconductor device according to claim ~~21~~, comprising a plurality of the cells, a gate pad disposed adjacent to the first source via hole, and a drain pad disposed adjacent to the second source via hole, wherein the source

electrodes which are connected to the first source via hole outnumber the source electrodes which are connected to the second source via hole.

6. (Currently Amended) The semiconductor device according to claim 1, comprising a plurality of the cells and a plurality of gate wires to which any one of the ~~plurality of~~ gate electrodes is connected, wherein the gate wires are connected to a grounded capacitance via a resistor.

7. (Previously Presented) The semiconductor device according to claim 6, comprising an external connection pad which is connected to the resistor, wherein the external connection pad and the capacitance are connected by a wire.

8. (Previously Presented) A high power semiconductor device comprising:  
a plurality of source electrodes;  
an active region having an approximately rectangular shape, located on a semiconductor substrate;  
a plurality of source electrodes located on the active region;  
a drain electrode disposed such that the drain electrode faces the source electrodes across one of the gate electrodes; and  
a bridge wire disposed above the source electrodes and connecting the source electrodes to each other, wherein the source electrodes are connected with each other by the bridge wire so that currents carried by the source electrodes flow in directions alternately opposite to each other.

9. (Previously Presented) The semiconductor device according to claim 8, wherein the bridge wire includes first and second bridge wires, and the source electrodes connected with the first bridge wire and the source electrodes connected with the second bridge wire are disposed alternately.

10. (Previously Presented) The semiconductor device according to claim 8, wherein the bridge wire includes a plurality of bridge wires connecting the source electrodes which are adjacent to each other so that the plurality of source electrodes are connected in series.

11. (Previously Presented) The semiconductor device according to claim 8, comprising a plurality of gate wires to which any one of the plurality of gate electrodes is connected, wherein the gate wires are connected to a grounded capacitance via a resistor.

12. (Previously Presented) The semiconductor device according to claim 11, comprising an external connection pad which is connected to the resistor, wherein the external connection pad and the capacitance are connected by a wire.

13. (New) A high power semiconductor device comprising:  
an active region having an approximately rectangular shape, located on a semiconductor substrate;  
the plurality of drain electrodes extending across at least part of the active region;  
a plurality of gate electrodes extending across at least part of the active region;  
a plurality of source electrodes extending across at least part of the active region, each pair of source electrodes being disposed on opposite sides of one of the drain electrodes with respective gate electrodes interposed between the drain electrode and the source electrodes of the pair of source electrodes;  
a plurality of source via holes located on the semiconductor substrate outside of and on opposite sides of the active region; and  
a plurality of bridge wires disposed above the drain electrodes and connecting respective groups of the source electrodes to each other and to one of the source via holes so that currents carried by the respective groups of source electrodes flow in opposite directions from each other.

14. (New) The semiconductor device according to claim 13 wherein the bridge wires extend along a width direction of the source electrodes connected to the bridge wires.

15. (New) The semiconductor device according to claim 13, wherein the source via holes on opposite sides of the active region are not directly opposite each other but are offset relative to a direction along the source and drain electrodes extend on the active region.

16. (New) The semiconductor device according to claim 13, comprising a plurality of gate wires to which any one of the gate electrodes is connected, wherein the gate wires are connected to a grounded capacitance via a resistor.

17. (New) The semiconductor device according to claim 16, comprising an external connection pad which is connected to the resistor, wherein the external connection pad and the capacitance are connected by a wire.

18. (New) The semiconductor device according to claim 1 including a plurality of the cells and a plurality of bridge wires connecting source electrodes which are adjacent to each other so that the plurality of source electrodes are connected in series.